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(54) Title: METHODS FOR FABRICATING LINE/SPACE ROUTING BETWEEN C4 PADS

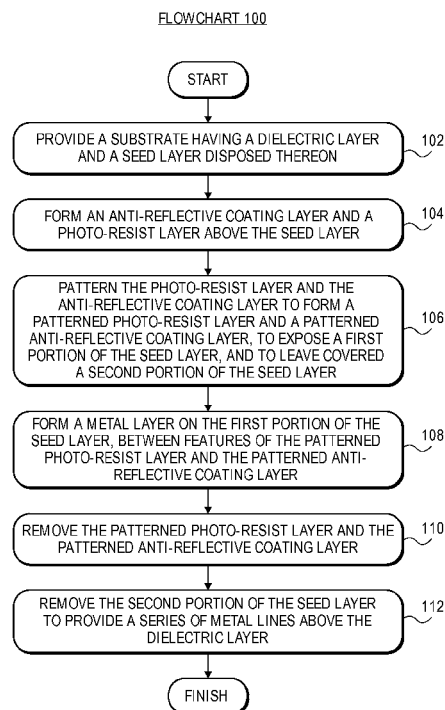


FIG. 1

(57) Abstract: A method for fabricating fine line and space routing described. The method includes providing a substrate having a dielectric layer and a seed layer disposed thereon. An anti-reflective coating layer and a photo-resist layer are then formed above the seed layer. The photo-resist layer and the anti-reflective coating layer are patterned to form a patterned photo-resist layer and a patterned anti-reflective coating layer, to expose a first portion of the seed layer, and to leave covered a second portion of the seed layer. A metal layer is then formed on the first portion of the seed layer, between features of the patterned photo-resist layer and the patterned anti-reflective coating layer. The patterned photo-resist layer and the patterned anti-reflective coating layer are subsequently removed. Then, the second portion of the seed layer is removed to provide a series of metal lines above the dielectric layer.



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